

# SCHOTTKY BARRIER DIODE

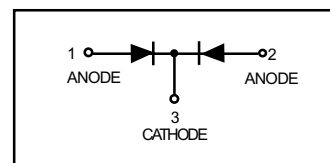
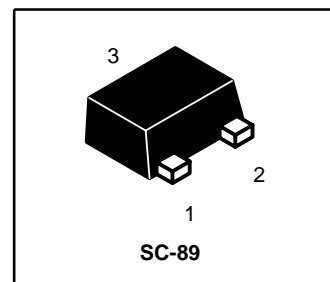
## ●Features

- Small surface mounting type SC-89
- Low  $V_F$  and low  $I_R$
- High reliability

## ●Construction

silicon epitaxial planar

**LRB715WT1**



## MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	40	V
DC reverse voltage	$V_R$	40	V
Mean rectifying current	$I_O$	30	mA
Peak forward surge current*	$I_{FSM}$	200	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40~+125	$^\circ\text{C}$

\* 60 Hz for 1  $\infty$

## DEVICE MARKING

LRB715WT1=3D

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.37	V	$I_F = 1\text{mA}$
Reverse current	$I_R$	-	-	1	$\mu\text{A}$	$V_R = 10\text{V}$
Capacitance between terminals	$C_T$	-	2.0	-	pF	$V_R = 1\text{V}, f = 1\text{MHz}$

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Electrical characteristic curves ( $T_A = 25^\circ\text{C}$ )

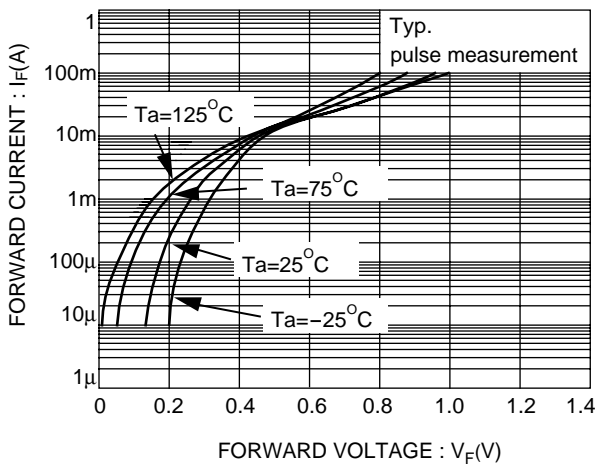


Fig. 1 Forward characteristics

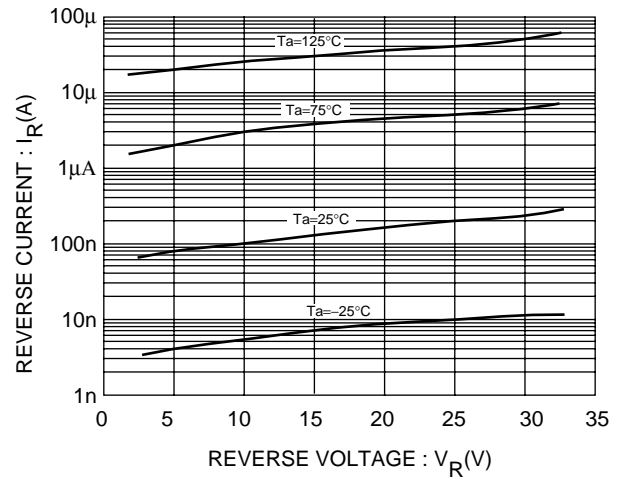


Fig. 2 Reverse characteristics

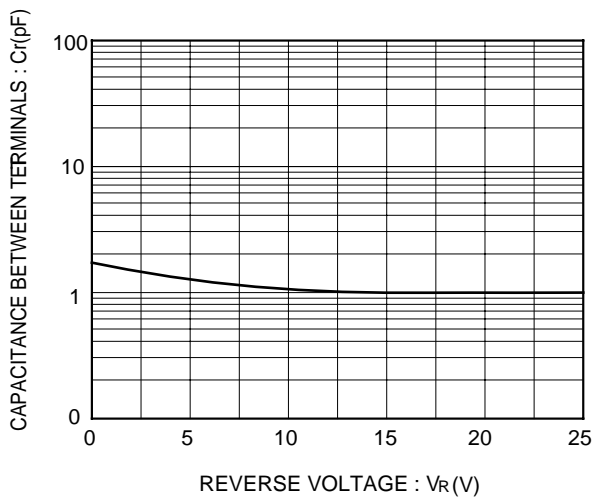


Fig. 3 Capacitance between terminals characteristics

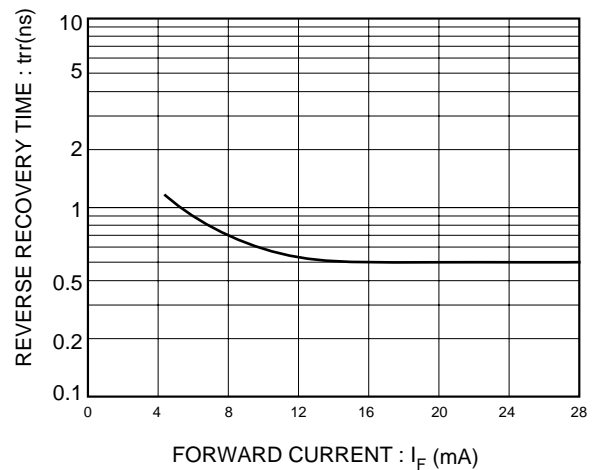
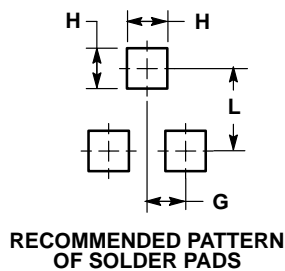
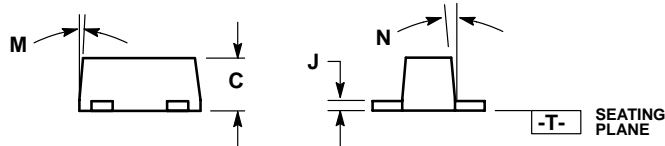
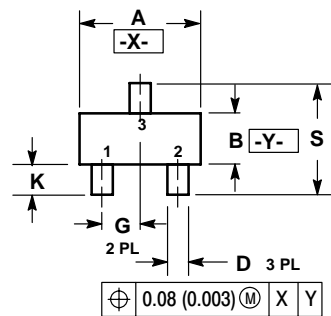


Fig. 4 Reverse recovery time characteristics

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SC-89



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067